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# Power Matters<sup>™</sup>

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### 2N5348 (#23370)

## Products

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#### Overview

Electrical Rating	Symb	ol	Min		Тур	Max	Unit
Collector to Emitter Saturation Voltage	V <sub>CE(sa</sub>	at)				0.70	V
DC Current Gain	HFE		30.00	)		120.00	
Maximum Electrical Rating		Sym	nbol	Min	Тур	Max	Unit
Maximum Electrical Rating  Breakdown Voltage, Collector-Base (Emitter Open)			nbol	Min	Тур	Max 100.00	Unit
<u> </u>				Min	Тур		
Breakdown Voltage, Collector-Base (Emitter Open)		V <sub>BR</sub>	(CBO)	Min	Тур	100.00	V
Breakdown Voltage, Collector-Base (Emitter Open) Collector Current (dc)		V <sub>BR</sub>	C(CBO)	Min	Тур	100.00	V

#### This part can be found in the following product categories:

- ▶ Discretes ▶ Transistors ▶ BJT( BiPolar Junction Transistor) ▶ PNP Transistor
- Non-Radiation Hardened Devices ▶ Transistors ▶ BJT( BiPolar Junction Transistor) ▶ NPN Transistor

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